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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-fgg144t

Advanced Architecture

The proprietary Automotive ProASIC3 architecture provides granularity comparable to standard-cell ASICs. The Automotive ProASIC3 device consists of five distinct and programmable architectural features (Figure 1-1 and Figure 1-2 on page 1-4):

- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM memory
- Extensive CCCs and PLLs
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the Automotive ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation-architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

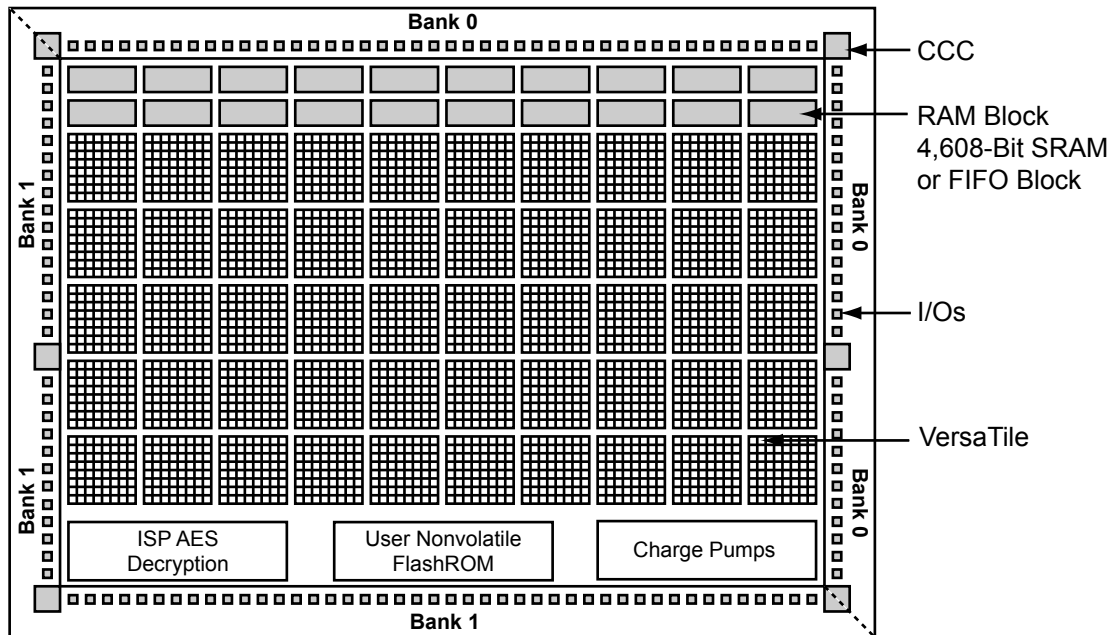


Figure 1-1 • Automotive ProASIC3 Device Architecture Overview with Two I/O Banks (A3P060 and A3P125)

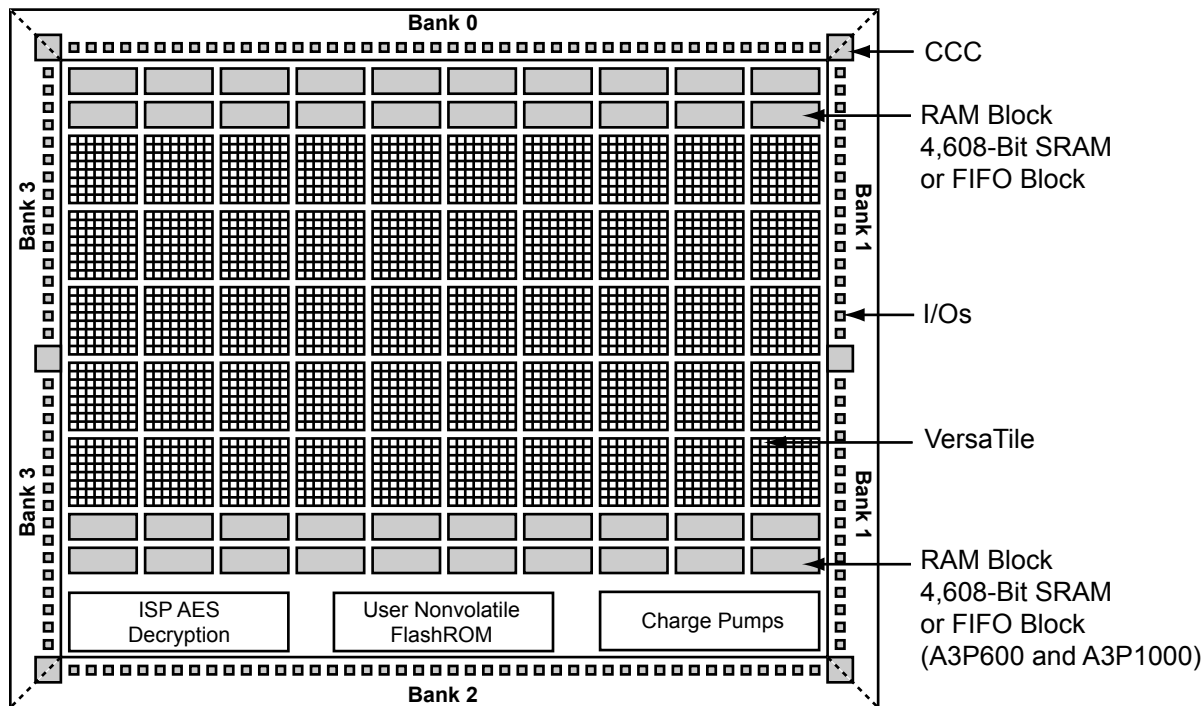


Figure 1-2 • Automotive ProASIC3 Device Architecture Overview with Four I/O Banks (A3P600 and A3P1000)

VersaTiles

The Automotive ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS}® core tiles. The Automotive ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.

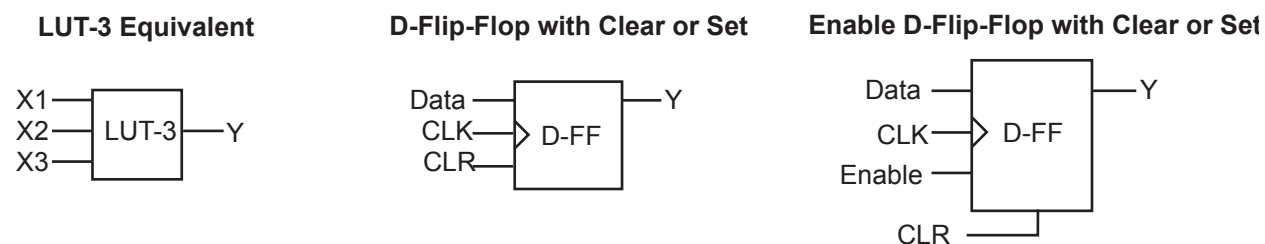


Figure 1-3 • VersaTile Configurations

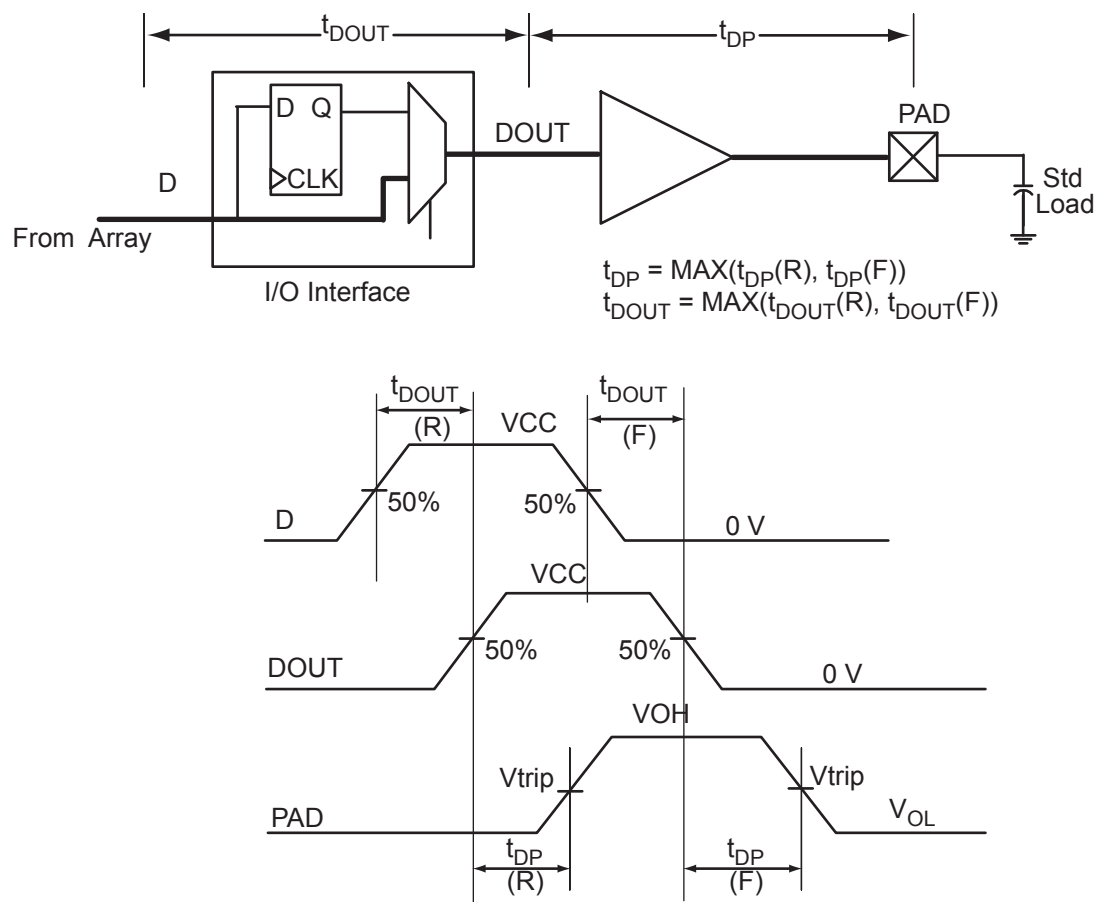


Figure 2-5 • Output Buffer Model and Delays (example)

Table 2-29 • I/O Short Currents IOSH/IOSL
Applicable to Standard Plus I/O Banks

	Drive Strength	I _{OSL} (mA)*	I _{OSH} (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	109	103
2.5 V LVCMOS	2 mA	18	16
	6 mA	37	32
	12 mA	74	65
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	44	35
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	109	103

Note: *T_J = 100°C

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 110°C, the short current condition would have to be sustained for more than three months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-30 • Duration of Short Circuit Event before Failure

Temperature	Time before Failure
–40°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months
110°C	3 months
125°C	25 days
135°	12 days

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-43 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
2 mA	-0.3	0.7	1.7	3.6	0.7	1.7	2	2	18	16	10	10
6 mA	-0.3	0.7	1.7	3.6	0.7	1.7	6	6	37	32	10	10
12 mA	-0.3	0.7	1.7	3.6	0.7	1.7	12	12	74	65	10	10
16 mA	-0.3	0.7	1.7	3.6	0.7	1.7	16	16	87	83	10	10
24 mA	-0.3	0.7	1.7	3.6	0.7	1.7	24	24	124	169	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 125°C junction temperature.
3. Software default selection highlighted in gray.

Table 2-44 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max., mA ¹	Max., mA ¹	μA ²	μA ²
2 mA	-0.3	0.7	1.7	3.6	0.7	1.7	2	2	18	16	10	10
6 mA	-0.3	0.7	1.7	3.6	0.7	1.7	6	6	37	32	10	10
12 mA	-0.3	0.7	1.7	3.6	0.7	1.7	12	12	74	65	10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 125°C junction temperature.
3. Software default selection highlighted in gray.

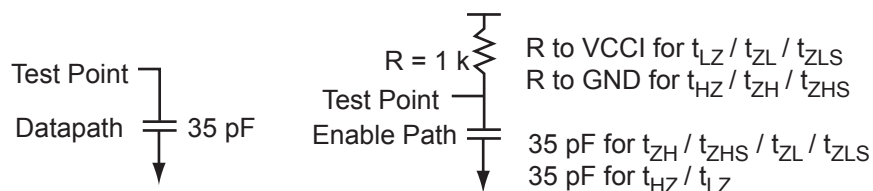


Figure 2-8 • AC Loading

Table 2-45 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	2.5	1.2	35

Note: *Measuring point = V_{trip}. See Table 2-18 on page 2-17 for a complete table of trip points.

Table 2-50 • 2.5 V LVCMOS High Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	9.37	0.05	1.40	0.45	8.47	9.37	1.43	1.21	10.89	11.79	ns
	-1	0.53	7.97	0.04	1.19	0.38	7.21	7.97	1.43	1.21	9.27	10.03	ns
6 mA	STD	0.63	5.59	0.05	1.40	0.45	5.45	5.59	1.63	1.57	7.87	8.01	ns
	-1	0.53	4.75	0.04	1.19	0.38	4.63	4.75	1.63	1.57	6.69	6.81	ns
12 mA	STD	0.63	3.85	0.05	1.40	0.45	3.92	3.71	1.77	1.80	6.34	6.13	ns
	-1	0.53	3.28	0.04	1.19	0.38	3.34	3.16	1.77	1.80	5.39	5.22	ns
16 mA	STD	0.63	3.63	0.05	1.40	0.45	1.79	1.64	3.64	3.84	2.96	2.83	ns
	-1	0.53	3.08	0.04	1.19	0.38	1.79	1.64	3.09	3.27	2.96	2.83	ns
24 mA	STD	0.63	3.34	0.05	1.40	0.45	1.65	1.31	3.72	4.32	2.82	2.50	ns
	-1	0.53	2.84	0.04	1.19	0.38	1.65	1.31	3.16	3.68	2.82	2.50	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-51 • 2.5 V LVCMOS Low Slew

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	11.73	0.05	1.40	0.45	12.14	12.33	1.43	1.16	14.55	14.75	ns
	-1	0.53	9.98	0.04	1.19	0.38	10.32	10.49	1.43	1.16	12.38	12.55	ns
6 mA	STD	0.63	7.97	0.05	1.40	0.45	8.77	8.45	1.63	1.51	11.19	10.87	ns
	-1	0.53	6.78	0.04	1.19	0.38	7.46	7.19	1.63	1.52	9.52	9.25	ns
12 mA	STD	0.63	6.68	0.05	1.40	0.45	6.81	6.40	1.77	1.74	9.23	8.82	ns
	-1	0.53	5.69	0.04	1.19	0.38	5.79	5.45	1.77	1.74	7.85	7.50	ns
16 mA	STD	0.63	6.24	0.05	1.40	0.45	6.35	5.98	1.80	1.80	8.77	8.40	ns
	-1	0.53	5.30	0.04	1.19	0.38	5.40	5.08	1.80	1.80	7.46	7.14	ns
24 mA	STD	0.63	5.96	0.05	1.40	0.45	5.95	5.96	1.84	2.03	8.37	8.38	ns
	-1	0.53	5.07	0.04	1.19	0.38	5.06	5.07	1.84	2.03	7.12	7.12	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-58 • 1.8 V LVC MOS Low Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	17.36	0.05	1.45	0.46	15.78	17.36	1.53	0.87	18.28	19.864	ns
	-1	0.55	14.77	0.04	1.23	0.39	13.42	14.77	1.54	0.87	15.55	16.897	ns
4 mA	STD	0.64	11.71	0.05	1.45	0.46	11.64	11.71	1.78	1.48	14.14	14.214	ns
	-1	0.55	9.96	0.04	1.23	0.39	9.90	9.96	1.78	1.48	12.03	12.091	ns
6 mA	STD	0.64	9.00	0.05	1.45	0.46	9.17	8.77	1.95	1.77	11.67	11.267	ns
	-1	0.55	7.66	0.04	1.23	0.39	7.80	7.46	1.95	1.77	9.92	9.585	ns
8 mA	STD	0.64	8.39	0.05	1.45	0.46	8.54	8.16	1.99	1.85	11.04	10.66	ns
	-1	0.55	7.14	0.04	1.23	0.39	7.27	6.94	1.99	1.85	9.40	9.068	ns
12 mA	STD	0.64	8.15	0.05	1.45	0.46	8.09	8.15	2.05	2.14	10.59	10.654	ns
	-1	0.55	6.94	0.04	1.23	0.39	6.88	6.94	2.05	2.14	9.01	9.063	ns
16 mA	STD	0.64	8.15	0.05	1.45	0.46	8.09	8.15	2.05	2.14	10.59	10.654	ns
	-1	0.55	6.94	0.04	1.23	0.39	6.88	6.94	2.05	2.14	9.01	9.063	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

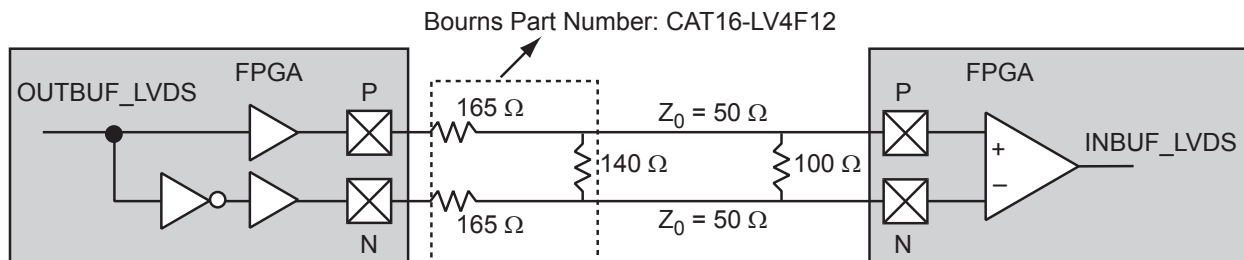
Table 2-59 • 1.8 V LVC MOS High Slew

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	13.26	0.05	1.36	0.46	9.75	12.67	1.24	0.82	12.26	15.17	ns
	-1	0.55	11.28	0.04	1.16	0.39	8.30	10.78	1.24	0.83	10.43	12.905	ns
4 mA	STD	0.64	7.73	0.05	1.36	0.46	6.13	7.25	1.46	1.41	8.63	9.749	ns
	-1	0.55	6.58	0.04	1.16	0.39	5.21	6.17	1.46	1.41	7.34	8.293	ns
6 mA	STD	0.64	4.97	0.05	1.36	0.46	4.29	4.54	1.62	1.68	6.79	7.039	ns
	-1	0.55	4.23	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.987	ns
8 mA	STD	0.64	4.39	0.05	1.36	0.46	4.29	4.54	1.62	1.68	6.79	7.039	ns
	-1	0.55	3.73	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.987	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.


Figure 2-12 • LVDS Circuit Diagram and Board-Level Implementation
Table 2-82 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Typ.	Max.	Units
VCCI	Supply Voltage	2.375	2.5	2.625	V
VOL	Output Low Voltage	0.9	1.075	1.25	V
VOH	Output High Voltage	1.25	1.425	1.6	V
VI	Input Voltage	0	–	2.925	V
VODIFF	Differential Output Voltage	250	350	450	mV
VOCM	Output Common-Mode Voltage	1.125	1.25	1.375	V
VICM	Input Common-Mode Voltage	0.05	1.25	2.35	V
VIDIFF	Input Differential Voltage	100	350	–	mV

Table 2-83 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.075	1.325	Cross point

Note: *Measuring point = V_{trip} . See Table 2-18 on page 2-17 for a complete table of trip points.

Timing Characteristics

Table 2-84 • LVDS

Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.64	2.05	0.05	1.79	ns
–1	0.55	1.74	0.04	1.52	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-85 • LVDS

Automotive-Case Conditions: $T_J = 115^{\circ}\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.63	1.98	0.05	1.73	ns
–1	0.53	1.68	0.04	1.47	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

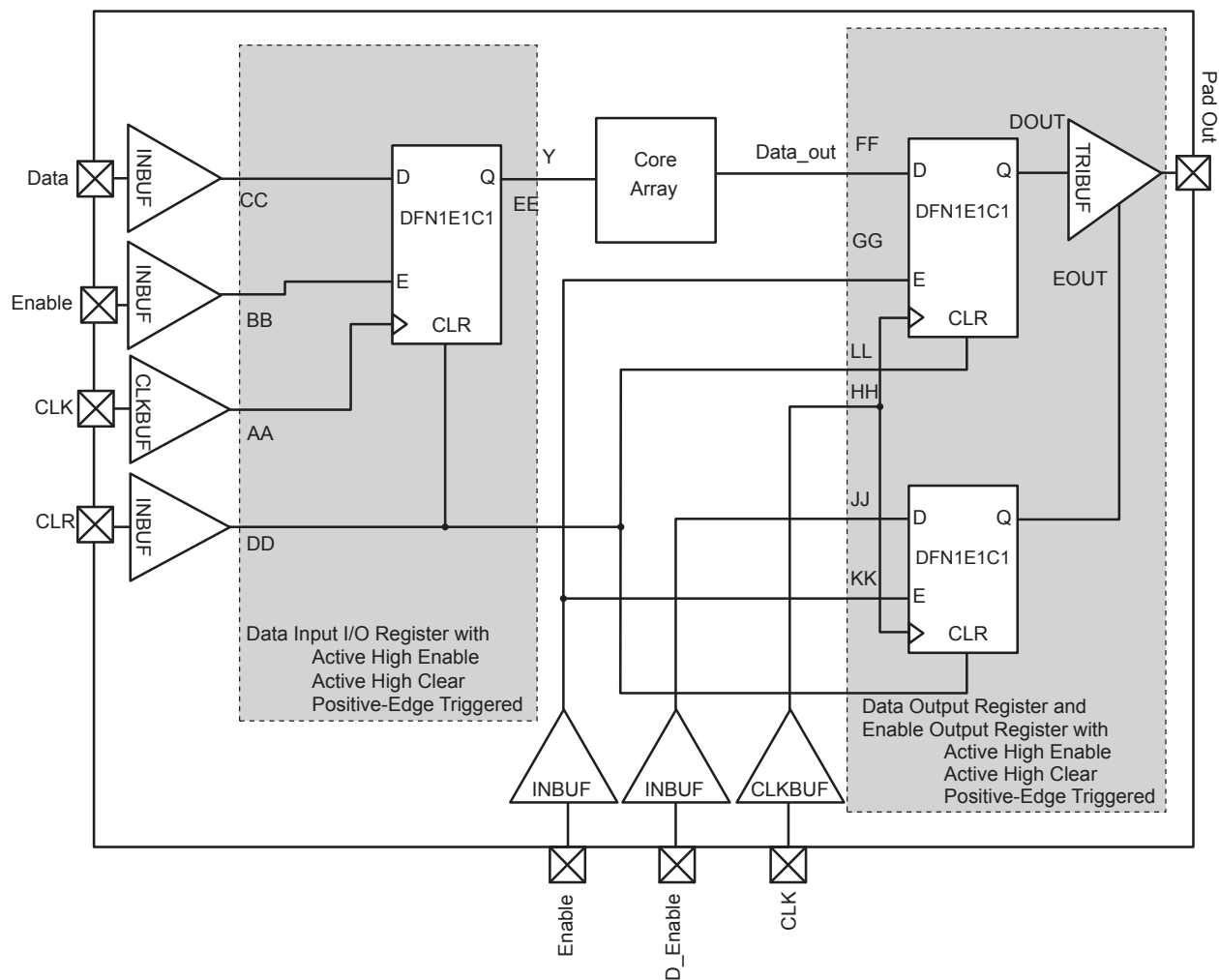


Figure 2-16 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear

Output Register

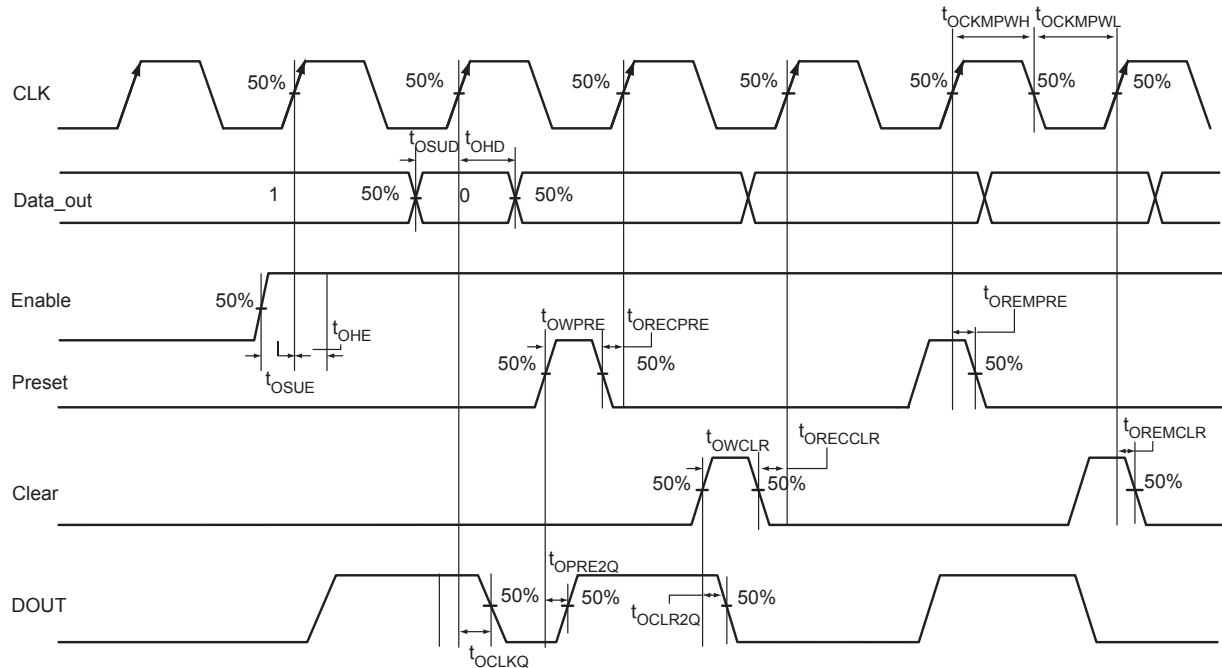


Figure 2-18 • Output Register Timing Diagram

Timing Characteristics

Table 2-94 • Output Data Register Propagation Delays
Automotive-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-1	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	0.72	0.84	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.38	0.45	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	0.00	ns
t_{OSUE}	Enable Setup Time for the Output Data Register	0.53	0.63	ns
t_{OHE}	Enable Hold Time for the Output Data Register	0.00	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	0.98	1.15	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	0.98	1.15	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.27	0.32	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.27	0.32	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.25	0.30	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.25	0.30	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.41	0.48	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

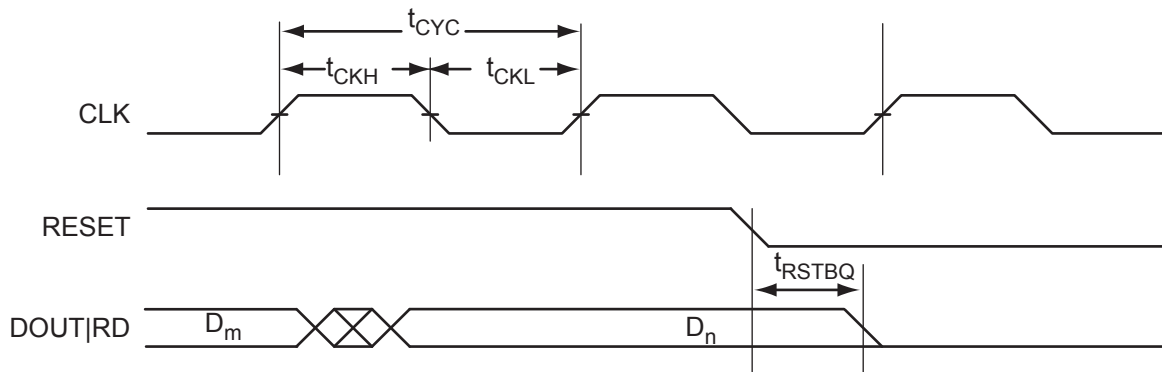


Figure 2-35 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18

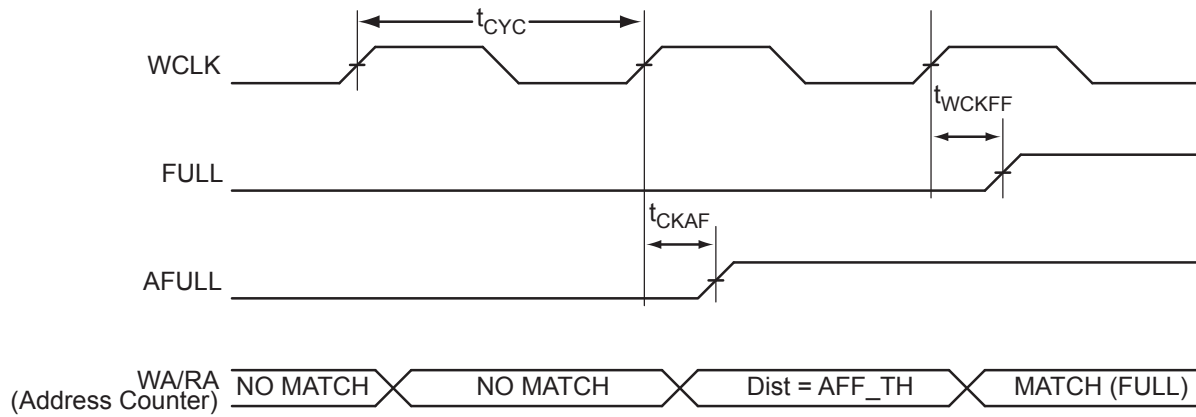
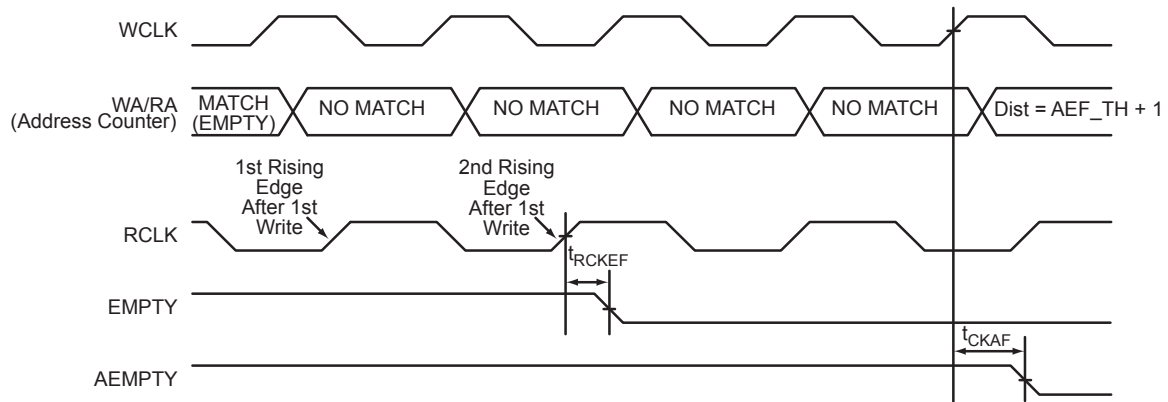
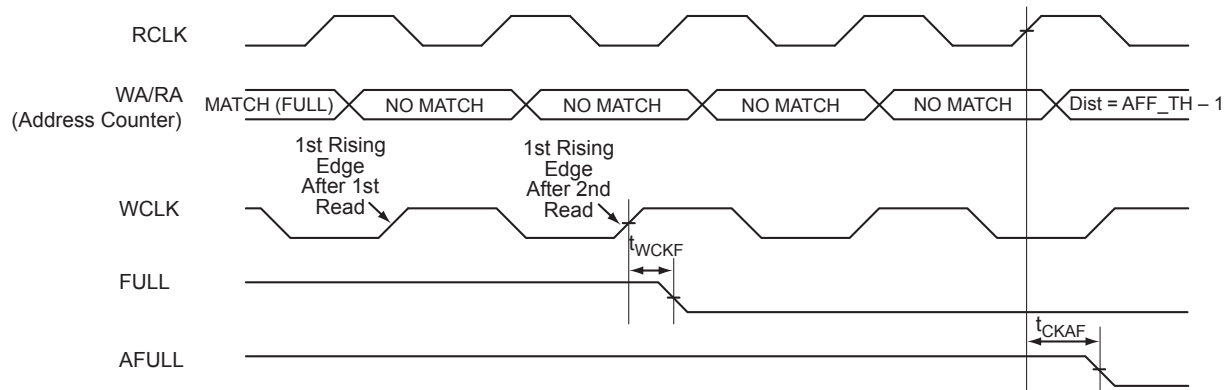

Figure 2-41 • FIFO FULL Flag and AFULL Flag Assertion

Figure 2-42 • FIFO EMPTY Flag and AEMPTY Flag Deassertion

Figure 2-43 • FIFO FULL Flag and AFULL Flag Deassertion

Table 2-122 • FIFO
Worst-Case Automotive Conditions: $T_J = 115^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.93	1.64	ns
t_{ENH}	REN, WEN Hold Time	0.03	0.02	ns
t_{BKS}	BLK Setup Time	0.27	0.32	ns
t_{BKH}	BLK Hold Time	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.26	0.22	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	3.30	2.81	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.25	1.07	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.41	2.05	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.29	1.95	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	8.68	7.38	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.37	2.02	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	8.59	7.30	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.29	1.10	ns
	RESET Low to Data Out Low on RD (pipelined)	1.29	1.10	ns
t_{REMRSTB}	RESET Removal	0.40	0.34	ns
t_{RECRSTB}	RESET Recovery	2.10	1.79	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.30	0.25	ns
t_{CYC}	Clock Cycle Time	4.53	3.85	ns
F_{MAX}	Maximum Frequency for FIFO	221	260	MHz

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

JTAG 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the ["User I/O Characteristics" section on page 2-12](#) for more details.

Timing Characteristics

Table 2-125 • JTAG 1532

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DISU}	Test Data Input Setup Time				ns
t_{DIHD}	Test Data Input Hold Time				ns
t_{TMSSU}	Test Mode Select Setup Time				ns
t_{TMDHD}	Test Mode Select Hold Time				ns
t_{TCK2Q}	Clock to Q (data out)				ns
t_{RSTB2Q}	Reset to Q (data out)				ns
F_{TCKMAX}	TCK Maximum Frequency	20	20	20	MHz
t_{TRSTREM}	ResetB Removal Time				ns
t_{TRSTREC}	ResetB Recovery Time				ns
t_{TRSTMPW}	ResetB Minimum Pulse				ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

QN132	
Pin Number	A3P125 Function
A1	GAB2/IO69RSB1
A2	IO130RSB1
A3	VCCIB1
A4	GFC1/IO126RSB1
A5	GFB0/IO123RSB1
A6	VCCPLF
A7	GFA1/IO121RSB1
A8	GFC2/IO118RSB1
A9	IO115RSB1
A10	VCC
A11	GEB1/IO110RSB1
A12	GEA0/IO107RSB1
A13	GEC2/IO104RSB1
A14	IO100RSB1
A15	VCC
A16	IO99RSB1
A17	IO96RSB1
A18	IO94RSB1
A19	IO91RSB1
A20	IO85RSB1
A21	IO79RSB1
A22	VCC
A23	GDB2/IO71RSB1
A24	TDI
A25	TRST
A26	GDC1/IO61RSB0
A27	VCC
A28	IO60RSB0
A29	GCC2/IO59RSB0
A30	GCA2/IO57RSB0
A31	GCA0/IO56RSB0
A32	GCB1/IO53RSB0
A33	IO49RSB0
A34	VCC
A35	IO44RSB0
A36	GBA2/IO41RSB0

QN132	
Pin Number	A3P125 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO68RSB1
B2	GAC2/IO131RSB1
B3	GND
B4	GFC0/IO125RSB1
B5	VCOMPLF
B6	GND
B7	GFB2/IO119RSB1
B8	IO116RSB1
B9	GND
B10	GEB0/IO109RSB1
B11	VMV1
B12	GEB2/IO105RSB1
B13	IO101RSB1
B14	GND
B15	IO98RSB1
B16	IO95RSB1
B17	GND
B18	IO87RSB1
B19	IO81RSB1
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO62RSB0

QN132	
Pin Number	A3P125 Function
B25	GND
B26	NC
B27	GCB2/IO58RSB0
B28	GND
B29	GCB0/IO54RSB0
B30	GCC1/IO51RSB0
B31	GND
B32	GBB2/IO43RSB0
B33	VMV0
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO67RSB1
C2	IO132RSB1
C3	VCC
C4	GFB1/IO124RSB1
C5	GFA0/IO122RSB1
C6	GFA2/IO120RSB1
C7	IO117RSB1
C8	VCCIB1
C9	GEA1/IO108RSB1
C10	GNDQ
C11	GEA2/IO106RSB1
C12	IO103RSB1
C13	VCCIB1
C14	IO97RSB1
C15	IO93RSB1
C16	IO89RSB1

FG144	
Pin Number	A3P060 Function
K1	GEB0/IO74RSB1
K2	GEA1/IO73RSB1
K3	GEA0/IO72RSB1
K4	GEA2/IO71RSB1
K5	IO65RSB1
K6	IO64RSB1
K7	GND
K8	IO57RSB1
K9	GDC2/IO56RSB1
K10	GND
K11	GDA0/IO50RSB0
K12	GDB0/IO48RSB0
L1	GND
L2	VMV1
L3	GEB2/IO70RSB1
L4	IO67RSB1
L5	VCCIB1
L6	IO62RSB1
L7	IO59RSB1
L8	IO58RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO69RSB1
M3	IO68RSB1
M4	IO66RSB1
M5	IO63RSB1
M6	IO61RSB1
M7	IO60RSB1
M8	NC
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	A3P125 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO11RSB0
A6	GND
A7	IO18RSB0
A8	VCC
A9	IO25RSB0
A10	GBA0/IO39RSB0
A11	GBA1/IO40RSB0
A12	GNDQ
B1	GAB2/IO69RSB1
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO08RSB0
B6	IO14RSB0
B7	IO19RSB0
B8	IO22RSB0
B9	GBB0/IO37RSB0
B10	GBB1/IO38RSB0
B11	GND
B12	VMV0
C1	IO132RSB1
C2	GFA2/IO120RSB1
C3	GAC2/IO131RSB1
C4	VCC
C5	IO10RSB0
C6	IO12RSB0
C7	IO21RSB0
C8	IO24RSB0
C9	IO27RSB0
C10	GBA2/IO41RSB0
C11	IO42RSB0
C12	GBC2/IO45RSB0

FG144	
Pin Number	A3P125 Function
D1	IO128RSB1
D2	IO129RSB1
D3	IO130RSB1
D4	GAA2/IO67RSB1
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO35RSB0
D8	GBC1/IO36RSB0
D9	GBB2/IO43RSB0
D10	IO28RSB0
D11	IO44RSB0
D12	GCB1/IO53RSB0
E1	VCC
E2	GFC0/IO125RSB1
E3	GFC1/IO126RSB1
E4	VCCIB1
E5	IO68RSB1
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO51RSB0
E9	VCCIB0
E10	VCC
E11	GCA0/IO56RSB0
E12	IO46RSB0
F1	GFB0/IO123RSB1
F2	VCOMPLF
F3	GFB1/IO124RSB1
F4	IO127RSB1
F5	GND
F6	GND
F7	GND
F8	GCC0/IO52RSB0
F9	GCB0/IO54RSB0
F10	GND
F11	GCA1/IO55RSB0
F12	GCA2/IO57RSB0

FG144	
Pin Number	A3P125 Function
G1	GFA1/IO121RSB1
G2	GND
G3	VCCPLF
G4	GFA0/IO122RSB1
G5	GND
G6	GND
G7	GND
G8	GDC1/IO61RSB0
G9	IO48RSB0
G10	GCC2/IO59RSB0
G11	IO47RSB0
G12	GCB2/IO58RSB0
H1	VCC
H2	GFB2/IO119RSB1
H3	GFC2/IO118RSB1
H4	GEC1/IO112RSB1
H5	VCC
H6	IO50RSB0
H7	IO60RSB0
H8	GDB2/IO71RSB1
H9	GDC0/IO62RSB0
H10	VCCIB0
H11	IO49RSB0
H12	VCC
J1	GEB1/IO110RSB1
J2	IO115RSB1
J3	VCCIB1
J4	GEC0/IO111RSB1
J5	IO116RSB1
J6	IO117RSB1
J7	VCC
J8	TCK
J9	GDA2/IO70RSB1
J10	TDO
J11	GDA1/IO65RSB0
J12	GDB1/IO63RSB0

FG144		FG144		FG144	
Pin Number	A3P250 Function	Pin Number	A3P250 Function	Pin Number	A3P250 Function
A1	GNDQ	D1	IO112NDB3	G1	GFA1/IO108PPB3
A2	VMV0	D2	IO112PDB3	G2	GND
A3	GAB0/IO02RSB0	D3	IO116VDB3	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO118UPB3	G4	GFA0/IO108NPB3
A5	IO16RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO29RSB0	D7	GBC0/IO35RSB0	G7	GND
A8	VCC	D8	GBC1/IO36RSB0	G8	GDC1/IO58UPB1
A9	IO33RSB0	D9	GBB2/IO42PDB1	G9	IO53NDB1
A10	GBA0/IO39RSB0	D10	IO42NDB1	G10	GCC2/IO53PDB1
A11	GBA1/IO40RSB0	D11	IO43NPB1	G11	IO52NDB1
A12	GNDQ	D12	GCB1/IO49PPB1	G12	GCB2/IO52PDB1
B1	GAB2/IO117UDB3	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO110NDB3	H2	GFB2/IO106PDB3
B3	GAA0/IO00RSB0	E3	GFC1/IO110PDB3	H3	GFC2/IO105PSB3
B4	GAA1/IO01RSB0	E4	VCCIB3	H4	GEC1/IO100PDB3
B5	IO14RSB0	E5	IO118VPB3	H5	VCC
B6	IO19RSB0	E6	VCCIB0	H6	IO79RSB2
B7	IO22RSB0	E7	VCCIB0	H7	IO65RSB2
B8	IO30RSB0	E8	GCC1/IO48PDB1	H8	GDB2/IO62RSB2
B9	GBB0/IO37RSB0	E9	VCCIB1	H9	GDC0/IO58VPB1
B10	GBB1/IO38RSB0	E10	VCC	H10	VCCIB1
B11	GND	E11	GCA0/IO50NDB1	H11	IO54PSB1
B12	VMV1	E12	IO51NDB1	H12	VCC
C1	IO117VDB3	F1	GFB0/IO109NPB3	J1	GEB1/IO99PDB3
C2	GFA2/IO107PPB3	F2	VCOMPLF	J2	IO106NDB3
C3	GAC2/IO116UDB3	F3	GFB1/IO109PPB3	J3	VCCIB3
C4	VCC	F4	IO107NPB3	J4	GEC0/IO100NDB3
C5	IO12RSB0	F5	GND	J5	IO88RSB2
C6	IO17RSB0	F6	GND	J6	IO81RSB2
C7	IO24RSB0	F7	GND	J7	VCC
C8	IO31RSB0	F8	GCC0/IO48NDB1	J8	TCK
C9	IO34RSB0	F9	GCB0/IO49NPB1	J9	GDA2/IO61RSB2
C10	GBA2/IO41PDB1	F10	GND	J10	TDO
C11	IO41NDB1	F11	GCA1/IO50PDB1	J11	GDA1/IO60UDB1
C12	GBC2/IO43PPB1	F12	GCA2/IO51PDB1	J12	GDB1/IO59UDB1

FG256	
Pin Number	A3P250 Function
P9	IO76RSB2
P10	IO71RSB2
P11	IO66RSB2
P12	NC
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO60VDB1
R1	GEA1/IO98PDB3
R2	GEA0/IO98NDB3
R3	NC
R4	GEC2/IO95RSB2
R5	IO91RSB2
R6	IO88RSB2
R7	IO84RSB2
R8	IO80RSB2
R9	IO77RSB2
R10	IO72RSB2
R11	IO68RSB2
R12	IO65RSB2
R13	GDB2/IO62RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO94RSB2
T3	GEB2/IO96RSB2
T4	IO93RSB2
T5	IO90RSB2
T6	IO87RSB2
T7	IO83RSB2
T8	IO79RSB2
T9	IO78RSB2
T10	IO73RSB2
T11	IO70RSB2
T12	GDC2/IO63RSB2

FG256	
Pin Number	A3P250 Function
T13	IO67RSB2
T14	GDA2/IO61RSB2
T15	TMS
T16	GND



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